Electronic Supplementary Information

Catalytically converting the NO_x by difunctional Ni-Ga based oxides

catalyst

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Fig. S1. TEM images for the as-prepared samples. (a) $NiGa_2O_4$. (b) $Ni_{0.5}Zn_{0.5}Ga_2O_4$. (c) $Ni_{0.1}Zn_{0.9}Ga_2O_4$. (b) $ZnGa_2O_4$.





Fig. S2. N₂ adsorption-desorption measurement. (a)NiGa₂O₄.(b) $ZnGa_2O_4.(c)$ Ni_{0.9} $Zn_{0.1}Ga_2O_4$. The inset shows the pore diameter distribution.



Fig. S3. TEM images for the as-prepared $Ni_{0.9}Zn_{0.1}Ga_2O_4$ sample. Inset shows the the FFT pattern obtained from the HRTEM image. From the FFT pattern, wen can know that the (311) and (111) were the possibly exposed facets.

To demonstrate the possible exposed facets, the FFT pattern was obtained from the HRTEM image, as shown in Fig.S3. Noting that the crystal structure of Ni-Ga based catalyst is cubic, the facets could be identified by combining the two prior knowledge by indexing the corresponding FFT spots.



Fig. S4. Experimental and theoretical results for valence state change of Ni. (a) UV-vis light absorption spectra for $Ni_{0.1}Zn_{0.9}Ga_2O_4$ before and after heating at 300°C in NO. (b) Calculated UV-vis light absorption spectra for $ZnGa_2O_4$ before and after Ni partly replacing Ga (denoted as $Ni_{Ga}^{3+}-ZnGa_2O_4$).

The UV-Vis absorption spectra for the as-prepared Ni_{0.9}Zn_{0.1}Ga₂O₄ before and after heating at 300°C in NO were shown in Fig.S2a. After heating in NO, the light absorption edge of the Ni_{0.1}Zn_{0.9}Ga₂O₄ exhibited the obvious red-shift. The theoretical calculation method was used to confirm the nature of light absorption edge shift. The NiGa₂O₄ is a largely inverse spinel with about 92% of Ni²⁺ in the octahedral sites. In NiGa₂O₄, cations are distributed on tetrahedrally and octahedrally coordinated sublattices. Therefore, for simplification, the normal spinel ZnGa₂O₄ was used as a model compound to carry out the theoretical calculations. A theoretical model was constructed by Ni partly replacing Ga with a valence state change from Ni^{2+} to Ni^{3+} in ZnGa₂O₄ to explore the effect of the valence state change of Ni on the light absorption of Zn-modified NiGa₂O₄. The theoretical calculations indicated that after Ni replacing Ga with a valence state change from Ni²⁺ to Ni³⁺ in ZnGa₂O₄ the light absorption edge of ZnGa₂O₄ also presented a similar red-shift. Thus, we can concluded that Ni²⁺ is easier to be oxidized to Ni³⁺ (lose an electron) when occupying the octahedral sites such as in NiGa₂O₄, which is a largely inverse spinel with about 92% of Ni²⁺ in the octahedral sites.



Fig. S5. In-situ XPS analysis for Ni_{0.9}Zn_{0.1}Ga₂O₄ at room temperature and after heating at 300°C in NO. (a) Ga 3d. (b) Ni 2p. (c) Zn 2p. (b) O 1s.